Thin film processing : Growth Poly-Si film by Hot Wire CVD (HWCVD) technique

Equipment: Hot wire CVD system (In-house fabricated)

Photograph :

Basic Principle: Catalytic creaking of silane gas by tungsten hot filament.

Capabilities: Fully manual operation, substrate temperature upto 850 °C and filament temperature up to 2200 °C.,

Sample requirements: Max sample size 2” x 2”